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FEB 0 7 2005

Sheet 1

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

Complete if Known						
Application Number	10/654189					
Filing Date	Sept 3, 2003					
First Named Inventor	Ashton et al					
Art Unit	2824 2891					
Examiner Name	Wilson, Christian D.					
Attorney Docket Number	100201669-1					

			U. S. PATEN	DOCUMENTS	
Examiner Initials*	Cite No.1	Document Number Number-Kind Code ^{2 (f known)}	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
a	1	^{US-} 2002/0176349	11/28/2002	Gibson et al	
1	2	^{US-} 2004/0086802	5/6/2004	Gibson	
	3	^{US-} 3983542	9/28/1976	Ovshinsky	
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		FORE	GN PATENT DOCU	MENTS		
Examiner Initials*	Cite No.	Foreign Patent Document	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages	-
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Examiner Signature	Christian	Wilson.	Date Considered	3/23/08

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. Applicant's unique citation designation number (optional). See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. Applicant is to place a check mark here if English language Translation is attached.

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Sheet 1 of 5

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